

L Number	Hits	S arch T xt	DB	Time stamp
1	381	438/247,597.c ls.	USPAT	2003/03/31 17:22
2	844	438/627,643.ccls.	USPAT	2003/03/31 17:23
3	836	438/648,652.ccls.	USPAT	2003/03/31 17:23
4	1095	438/653,656.ccls.	USPAT	2003/03/31 17:23
5	431	438/658,659.ccls.	USPAT	2003/03/31 17:24
6	1040	438/685,687.ccls.	USPAT	2003/03/31 17:24
7	735	257/751.ccls.	USPAT	2003/03/31 17:25
8	61	besser-paul.in. buynoski-matthew.in. lopatin-sergey.in.	USPAT	2003/03/31 17:27
9	3	besser-paul.in. buynoski-matthew.in. lopatin-sergey.in.	US-PGPUB	2003/03/31 17:26
10	7	besser-paul.in. buynoski-matthew.in. lopatin-sergey.in.	EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:26
11	11714	(tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8	USPAT	2003/03/31 17:41
13	6482	((tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8) and (implant\$8 same metal\$8)	USPAT	2003/03/31 17:34
14	4073	((tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8) and (hafnium "hf" lanthanum "la" barium "ba" tin "sn" zinc "zn")	USPAT	2003/03/31 17:40
15	1704	((((tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8) and (hafnium "hf" lanthanum "la" barium "ba" tin "sn" zinc "zn")) and (implant\$8 same (hafnium "hf" lanthanum "la" barium "ba" tin "sn" zinc "zn"))	USPAT	2003/03/31 17:43
16	4981	(tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8	EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:44
17	631	((tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8) and (implant\$8 same (hafnium "hf" lanthanum "la" barium "ba" tin "sn" zinc "zn"))	EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:44
18	2478	(tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8	US-PGPUB	2003/03/31 17:44
19	383	((tantalum "ta" "tin" "ti" titanium "tisin" "w" "wn" tungsten) same implant\$8) and (implant\$8 same (hafnium "hf" lanthanum "la" barium "ba" tin "sn" zinc "zn"))	US-PGPUB	2003/03/31 17:44

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Ion Implantation Technology Proceedings, 1998 International Conference on , V 2 , Dec 1999

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